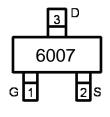
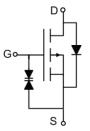


Main Product Characteristics:

V _{DSS}	-50V
R _{DS} (on)	2.1ohm(typ.)
I _D	-130mA







SOT-23

Marking and pin Assignment

Schematic diagram

Features and Benefits:

- Advanced MOSFET process technology
- Special designed for Line current interrupter in telephone sets, Relay, high speed and line transformer drivers and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance. These features combine to make this design an extremely efficient and reliable device for use in line current interrupter in telephone sets and a wide variety of other applications

Absolute max Rating:

Symbol	Parameter	Max.	Units
I _D @ TC = 25°C	Continuous Drain Current, V _{GS} @ -10V①	-130	
I _D @ TC = 100°C	Continuous Drain Current, V _{GS} @ -10V①	-100	mA
I _{DM}	Pulsed Drain Current②	-520	
P _D @TC = 25°C	Power Dissipation③	230	mW
V _{DS}	Drain-Source Voltage	-50	V
V _{GS}	Gate-to-Source Voltage	± 20	V
ESD	ESD Rating (HBM module)	1	KV
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Characterizes	Тур.	Max.	Units
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ④	_	556	°CM
	Junction-to-Ambient (PCB mounted, steady-state) ④	_	540	°CM



Electrical Characterizes @TA=25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-50	_	_	V	$V_{GS} = 0V, ID = -10\mu A$
R _{DS(on)}	Static Drain-to-Source on-resistance	_	2.1	7	Ω	V _{GS} =-10V,I _D = -130mA
$V_{GS(th)}$	Gate threshold voltage	-0.8	_	-2	V	$V_{DS} = V_{GS}, I_D = -1mA$
		_	_	-0.1		$V_{DS} = -40V, V_{GS} = 0V$
I _{DSS}	Drain-to-Source leakage current			-1	μA	$V_{DS} = -50 V, V_{GS} = 0 V$
		_	_	-50		T _J = 125°C
	Cata to Source forward lookage	_	_	10	uA	V _{GS} =20V
I _{GSS} (Gate-to-Source forward leakage	_	_	-10		V _{GS} = -20V
gfs	Forward Transconductance	50	_	_	S	V _{DS} =-25 V I _D =-130m A
C _{iss}	Input Capacitance	_	45	_		$V_{GS} = 0;$
C _{oss}	Output Capacitance	_	18	_	pF	$V_{DS} = -5 V;$
C _{rss}	Reverse Transfer Capacitance	_	11	_		f = 1 MHz
t _{d(on)}	Turn-On Delay Time	_	3.1	_		VDD = -15V;
t _r	Rise Time	_	1.3	_		ID = -2.5 A;
t _{d(off)}	Turn-Off Delay Time	_	18	_	ns	RL = 50ohm
t _f	Fall Time	_	7.5	_]	

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			130	mA	MOSFET symbol
	(Body Diode)	_				showing the
I _{SM}	Pulsed Source Current		_	520	mA	integral reverse
	(Body Diode)	_				p-n junction diode.
V _{SD}	Diode Forward Voltage	_	_	-1.3	V	I _S =-130mA, V _{GS} =0V

Notes:

- ①Calculated continuous current based on maximum allowable junction temperature.
- ②Repetitive rating; pulse width limited by max. junction temperature.
- ③The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- 4The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C

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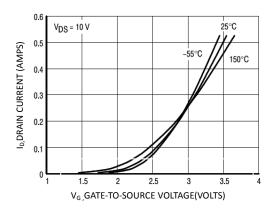


Fig 1: Transfer Characteristics

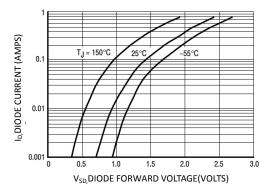


Fig 3: Body Diode Forward Curve

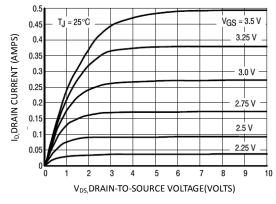


Fig 2: Output Curve

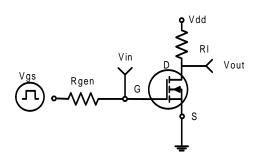


Fig 4: Switching Test Circuit

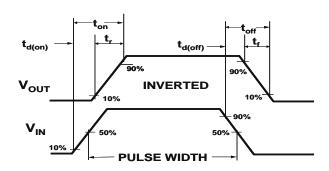
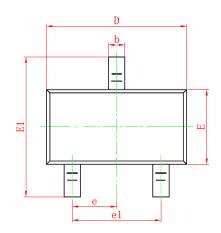


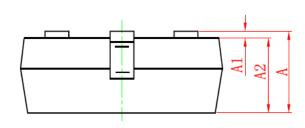
Fig 5: Switching Waveforms

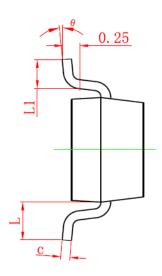


SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)







Cumbal	Dimensions in Millimeters			
Symbol	MIN.	MAX.		
Α	0.900	1.150		
A 1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0 °	8°		

Version: 1.1

NOTES

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.





Ordering and Marking Information

Device Marking: 6007

Package (Available)
SOT-23
Operating Temperature Range
C: -55 to 150 °C

Devices per Unit

Package	Units/	Tubes/	Units/	Inner Boxes/ Carton Box	Units/
Type	Tube	Inner Box	Inner Box		Carton Box
SOT23	3000pcs	10pcs	30000pcs	4pcs	120000pcs

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High	T _j = 150℃ @ 80% of	168 hours	3 lots x 77 devices
Temperature	Max V _{DSS} /V _{CES} /VR	500 hours	
Reverse		1000 hours	
Bias(HTRB)			
High	T _j = 150℃ @ 100% of	168 hours	3 lots x 77 devices
Temperature	Max V _{GSS}	500 hours	
Gate		1000 hours	
Bias(HTGB)			

Version: 1.1



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Customer Service

Worldwide Sales and Service:

Sales@silikron.com

Technical Support:

Technical@silikron.com

Suzhou Silikron Semiconductor Corp.

Building 11A Suchun Industrial Square, 428# Xinglong Street, Suzhou P.R. China

TEL: (86-512) 62560688 **FAX:** (86-512) 65160705 **E-mail:** Sales@silikron.com

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